

# Front-End electronics for Future Linear Collider W-Si calorimeter physics prototype

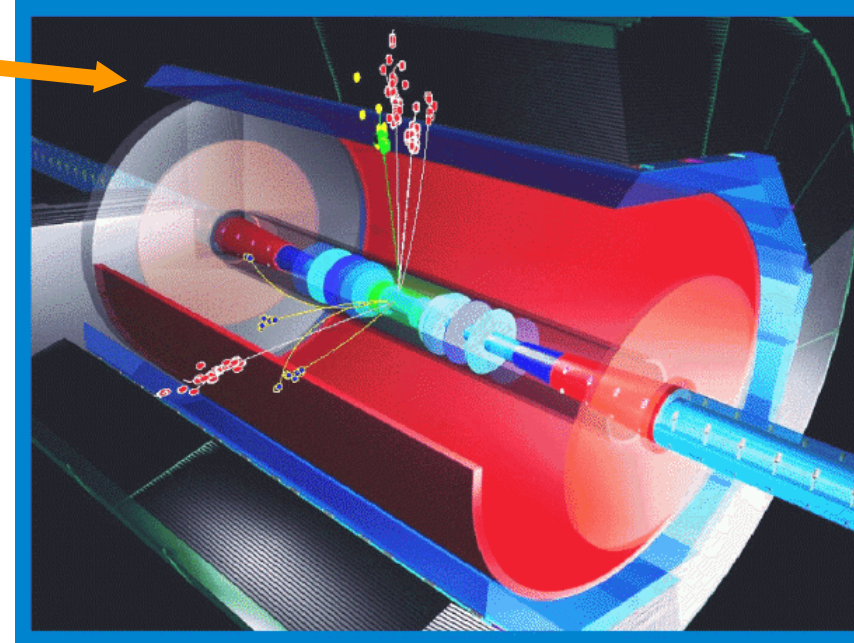
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LAL Orsay

<http://www.lal.in2p3.fr/technique/se/flc>

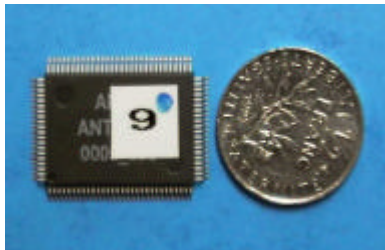
# Introduction : FLC challenges for electronics

## ■ CALICE = W-Si Calorimeter

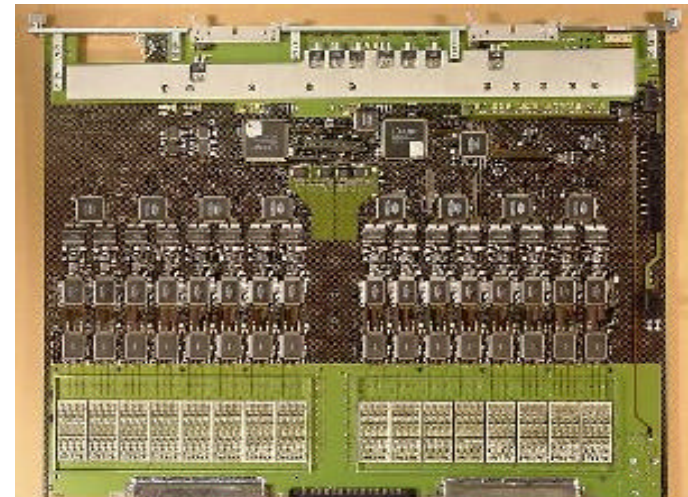
- Precision measurements :  $\sim 10\%/vE$ 
  - good linearity ( $\text{‰}$  level)
  - Good inter-calibration ( $\%$  level)
  - Low crosstalk ( $\text{‰}$  level)
- Large dynamic range
  - $0.1 \text{ MIP} \rightarrow 2500 \text{ MIPS} = 15 \text{ bits}$
- Low noise
  - Auto-trigger on MIP ( $40,000 e^-$ )
- Hermeticity : no room for electronics !
  - High level of integration : « SoC »
  - Ultra-low power : ( $\ll \text{mW/ch}$ )
- 30 Mchannels



## ■ « Tracker electronics with calorimetric performance »



FLC 128ch 30\*20mm 1 W ?

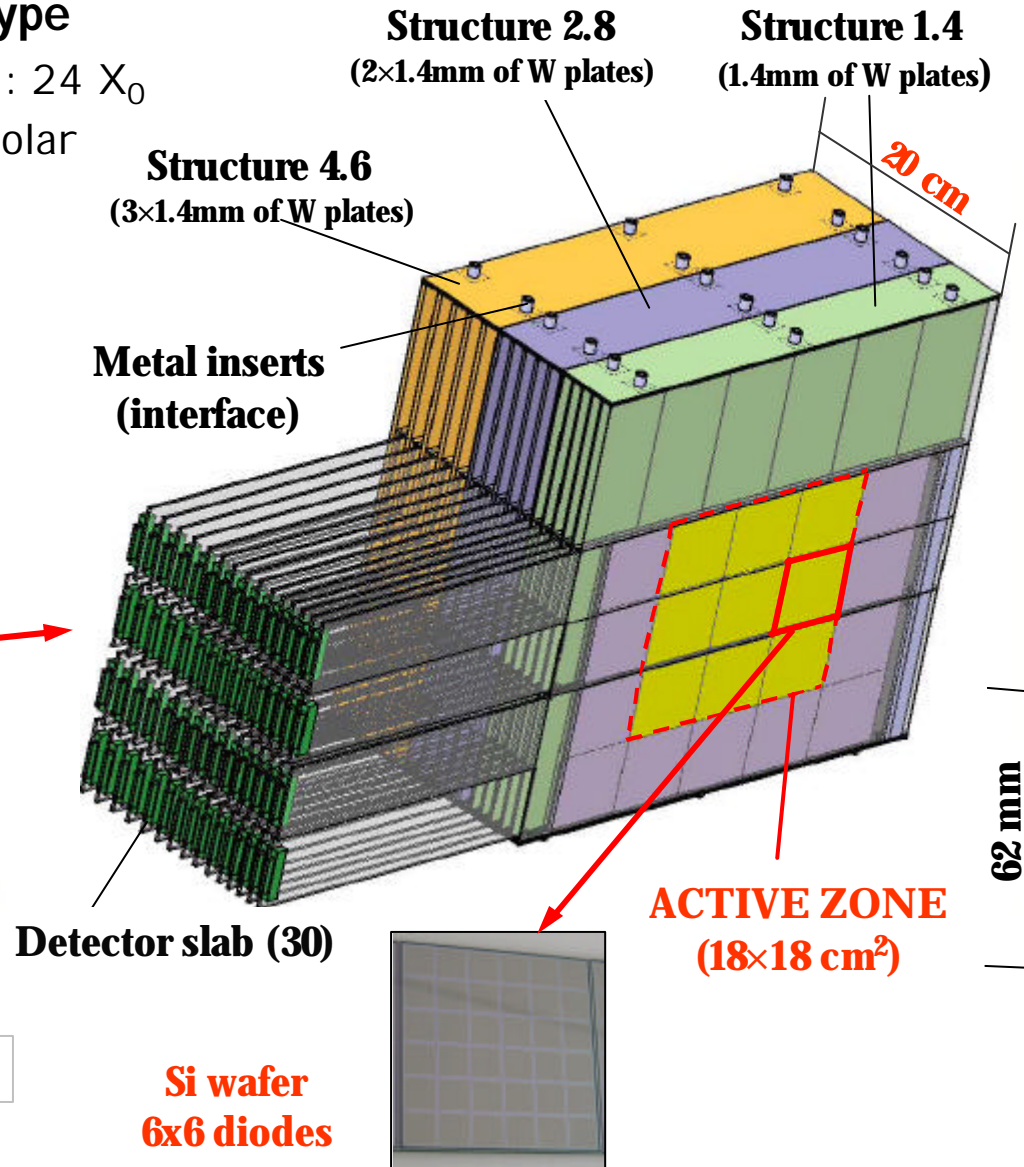
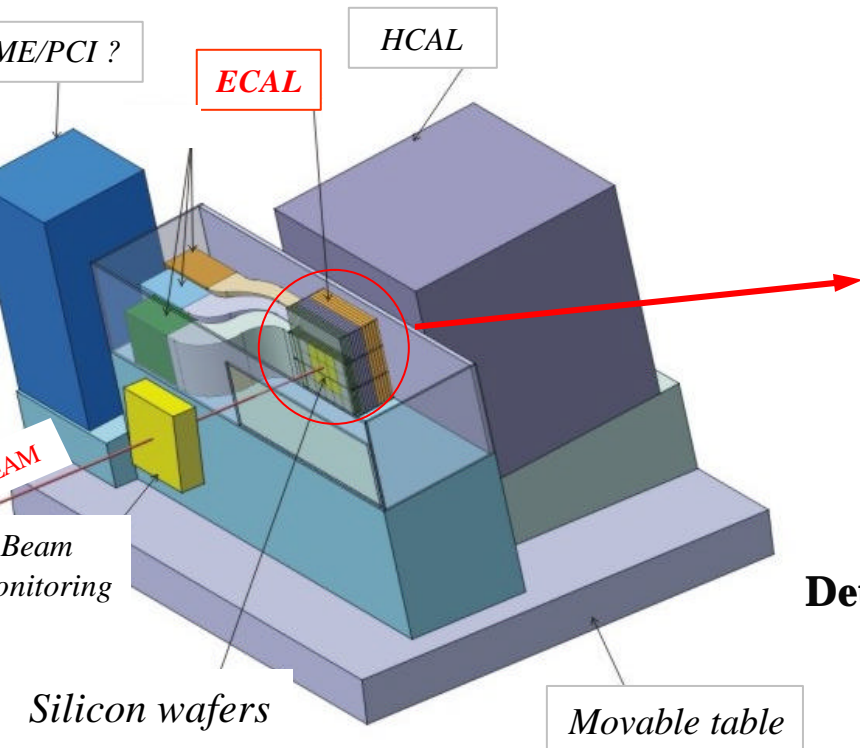


ATLAS LAr FEB 128ch 400\*500mm 100 W

# Physics prototype overview

## ■ Multi-layer (30) W-Si prototype

- Active area :  $18 \times 18 \text{ cm}^2$  , depth :  $24 X_0$
- 30 detector slabs slid into alveolar structure
- *See talk by J.C Brient*



# Silicon wafer description

[JC Vanel LLR lab]

## ■ Matrix of 6x6 pixels of 1 cm<sup>2</sup>

- Low cost => simple process
- 2 manufacturers :
  - INP Moscow
  - Institute of Physics Prague
- AC coupling on PCB

4" High resistive wafer : 5 K $\Omega$ cm

Thickness : 525 microns  $\pm$  3 %

Tile side :  $62.0^{+0}_{-0.1}$  mm

Guard ring

In Silicone  $\sim$ 80 e-h pairs / micron

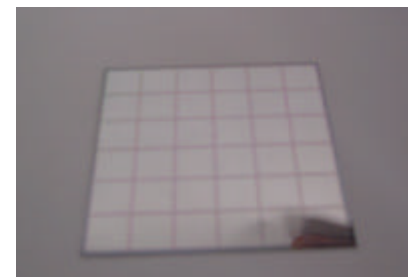
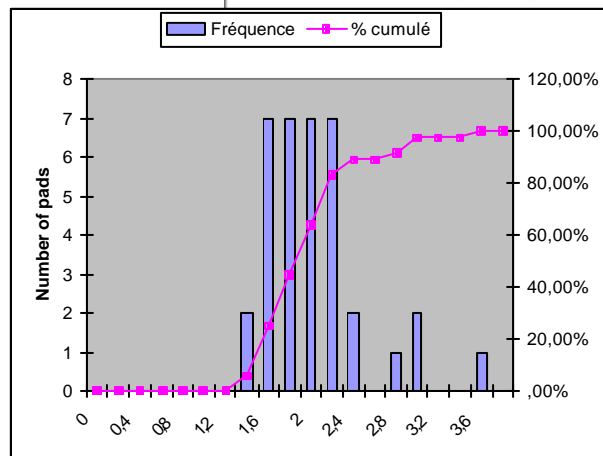
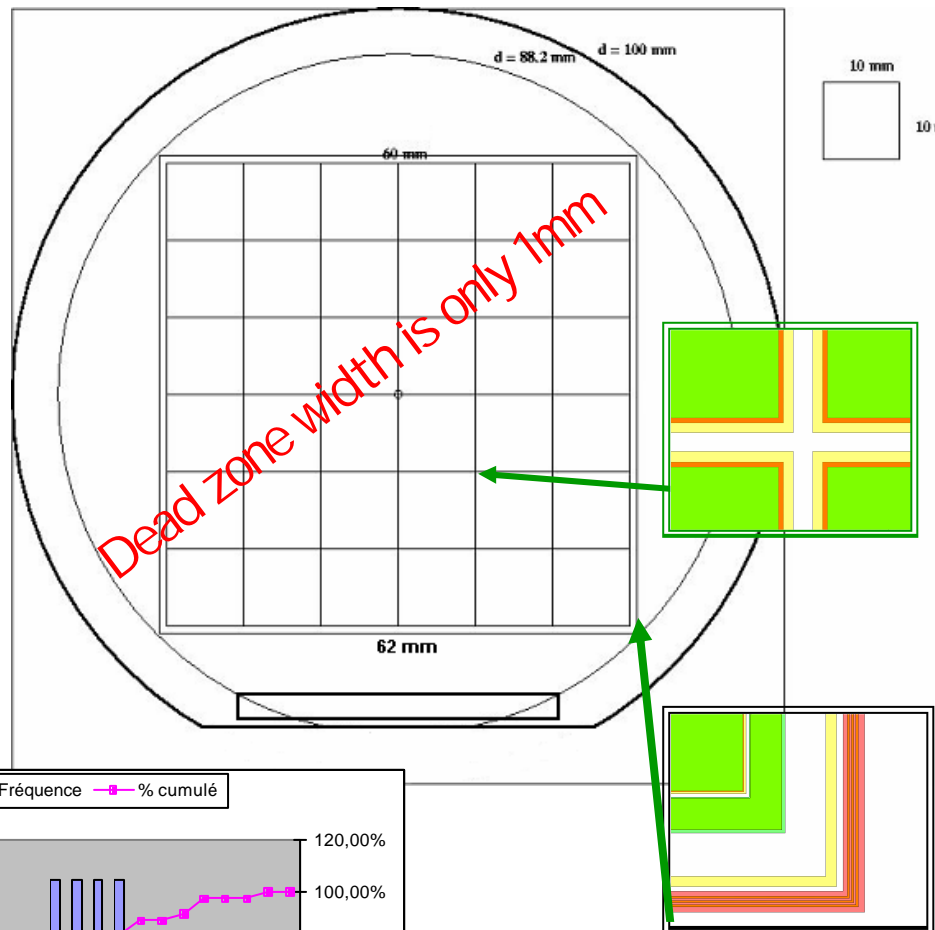
$\Rightarrow$  42000 e<sup>-</sup> /MiP

Capacitance :  $\sim$ 25 pF

Leakage current : 1 – 5 nA

Full depletion bias :  $\sim$ 150 V

Nominal operating bias : 200 V





# Front-end board

## 6 active wafers

Made of 36 silicon PIN diodes  
216 channels per board  
Each diode is a  $1\text{cm}^2$  square

## 2 calibration switches chips

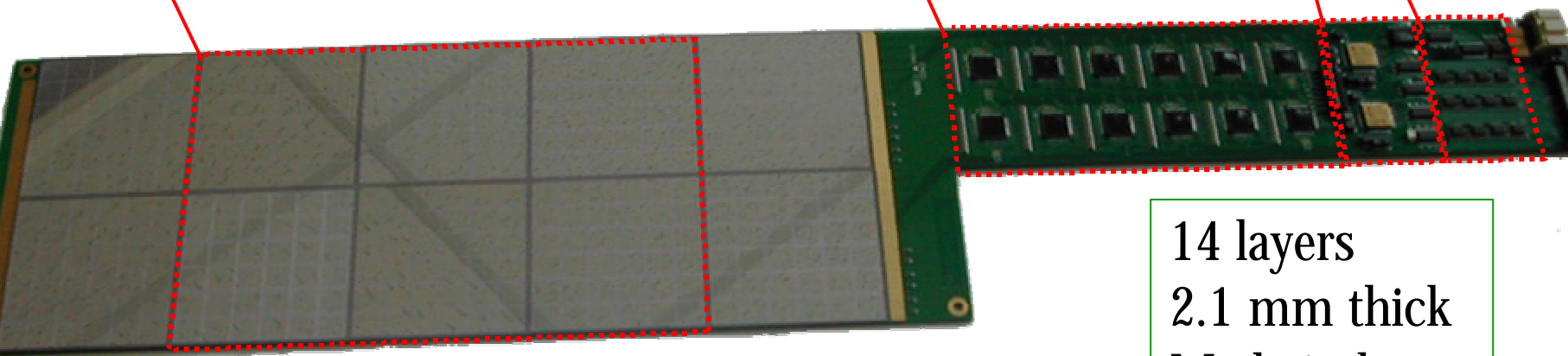
6 calibration channels per chip  
18 diodes per calibration channel  
*See talk on ATLAS calibration*

## 12 FLCPHY3 front-end chip

18 channels per chip  
13 bit dynamic range

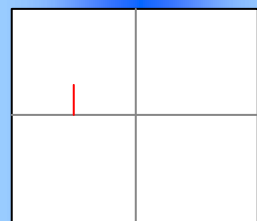
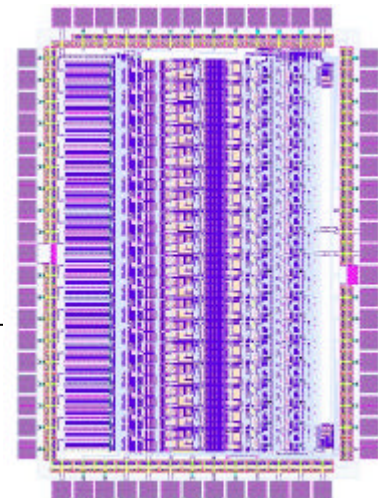
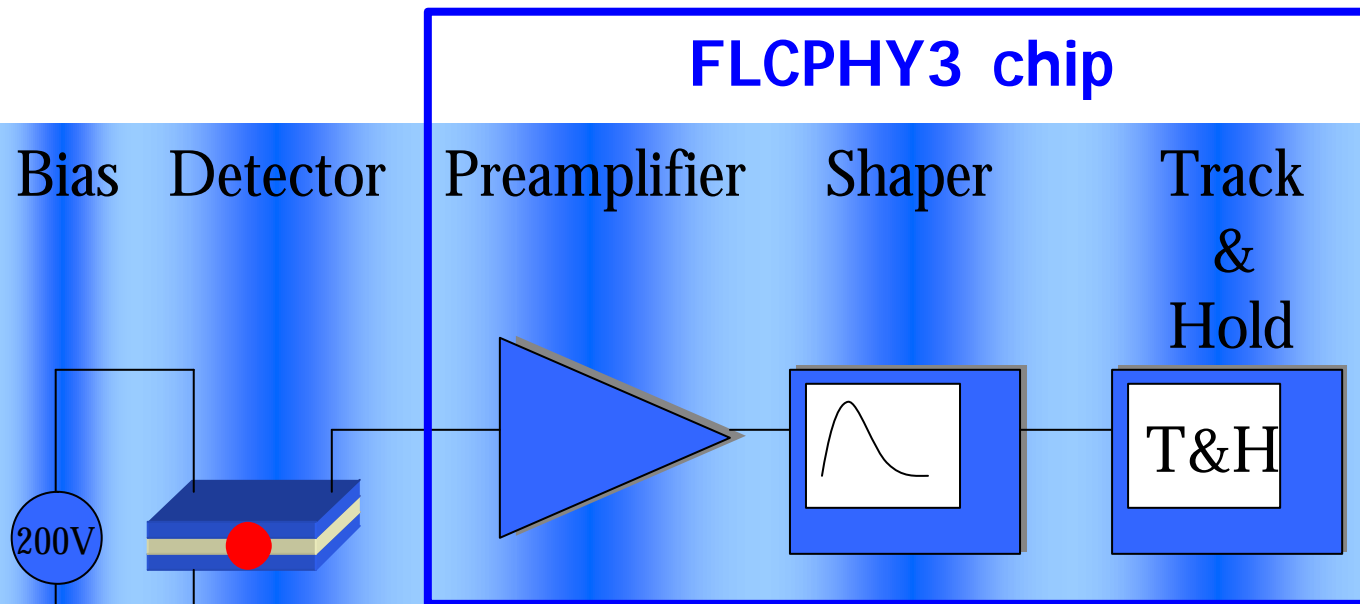
## Line buffers

To DAQ part  
Differential

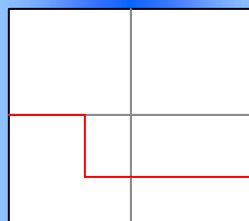


14 layers  
2.1 mm thick  
Made in korea

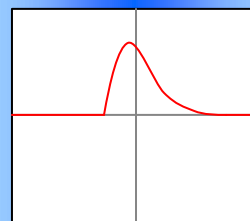
# Front-end electronics synoptic



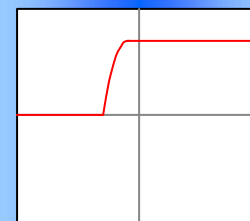
- PIN diode
- 10mm cells



- Variable gain
- High dyn. Range
- Low noise

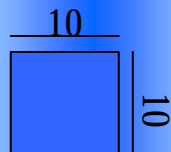


- dual gain
- 200 ns peaking time
- high linearity



## FLCPHY3

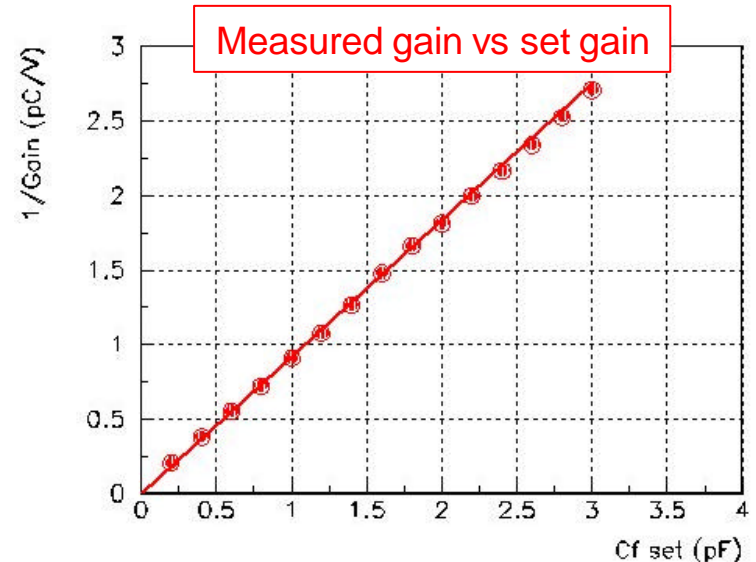
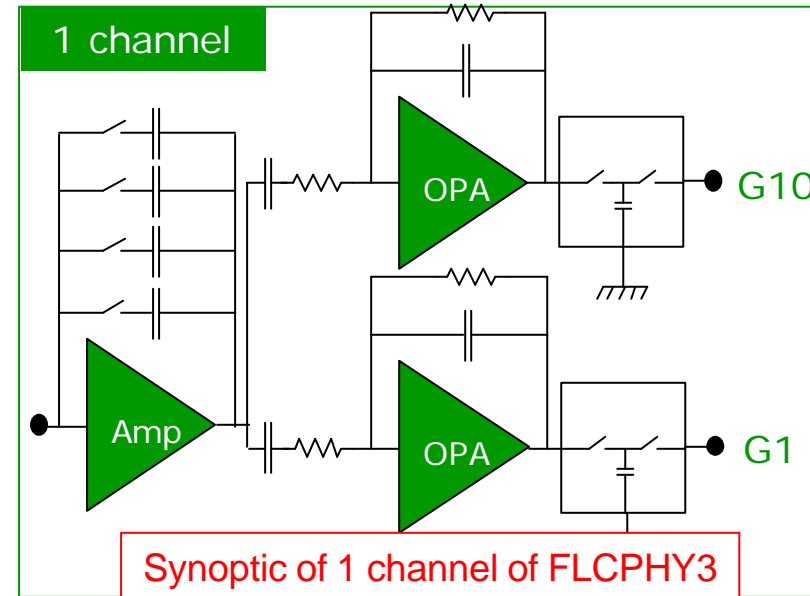
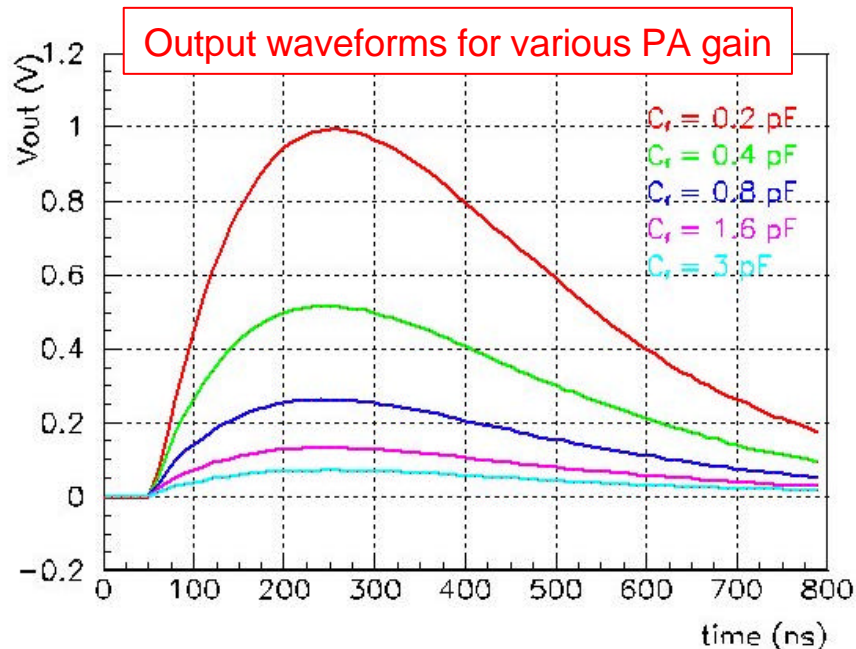
- BiCMOS 0.8 $\mu$ m
- 18 channels
- Area : 6 mm<sup>2</sup>
- $V_{SS} = -5V$
- $P_d = 250$  mW
- TQFP64 packg



# FLCPHY chip architecture

## Chip architecture

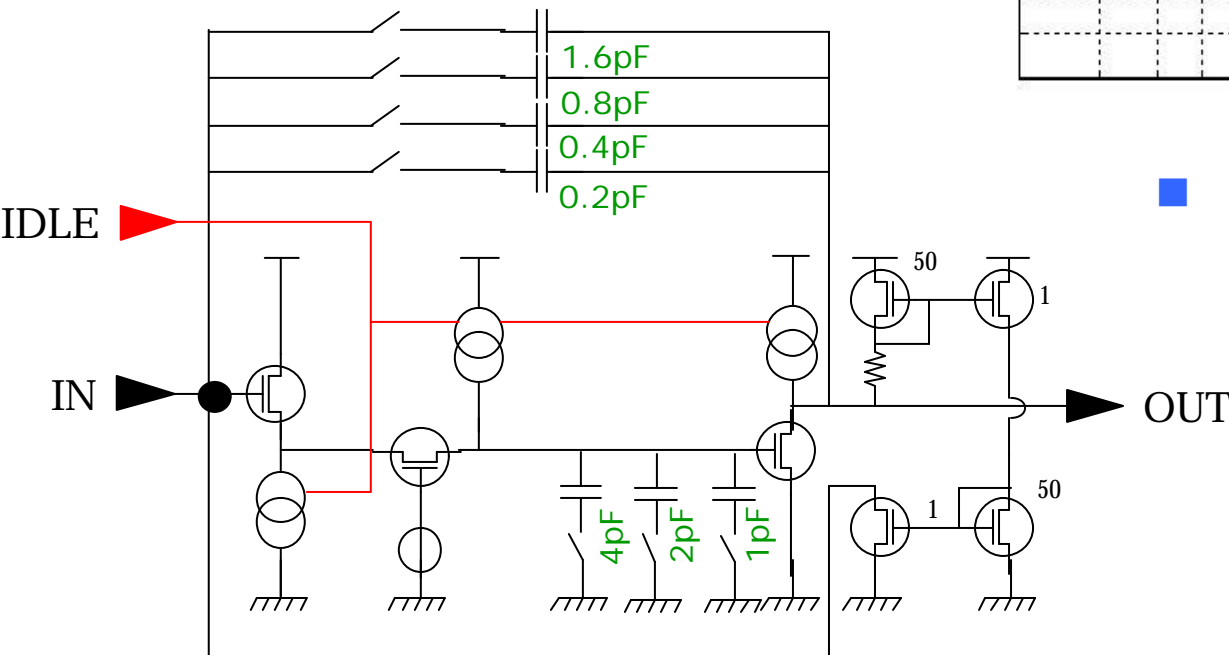
- Variable gain preamp ( $C_f = 0.2 \rightarrow 3$  pF) adapt to several detectors
- Dual gain shaper (G1-G10) -> possible studies with larger (16bit) dynamic range
- Differential shaper and Track&Hold => better pedestal stability and dispersion
- Multiplexed output : 5 MHz



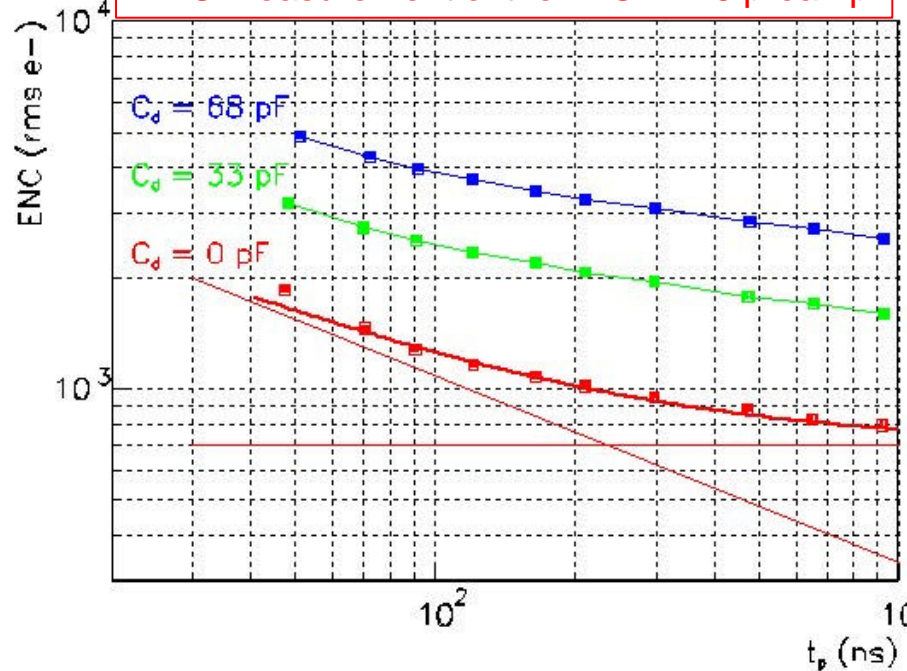
# Preamplifier performance : noise

## Charge preamp

- Folded cascode, negative output
- « mirror multiplied » feedback resistor, equivalent to 25 MO
- 3000/0.8 $\mu$ m PMOS input transistor
- $I_D = 600 \mu$ A bias current, 4mW total
- ENC = 1000e<sup>-</sup> + 40 e<sup>-</sup>/pF @  $t_p = 200$ ns



ENC measurement of the FLCPHY3 preamp



## Noise

- Series :  $e_n = 1.6$  nV/vHz
- $g_m = 8$  mA/V
- $C_{PA} = 10$  pF + 15 pF test board
- 1/f noise : 25e<sup>-</sup>/pF
- Parallel :  $i_n = 40$  fA/vHz



# Signal uniformity (G1)

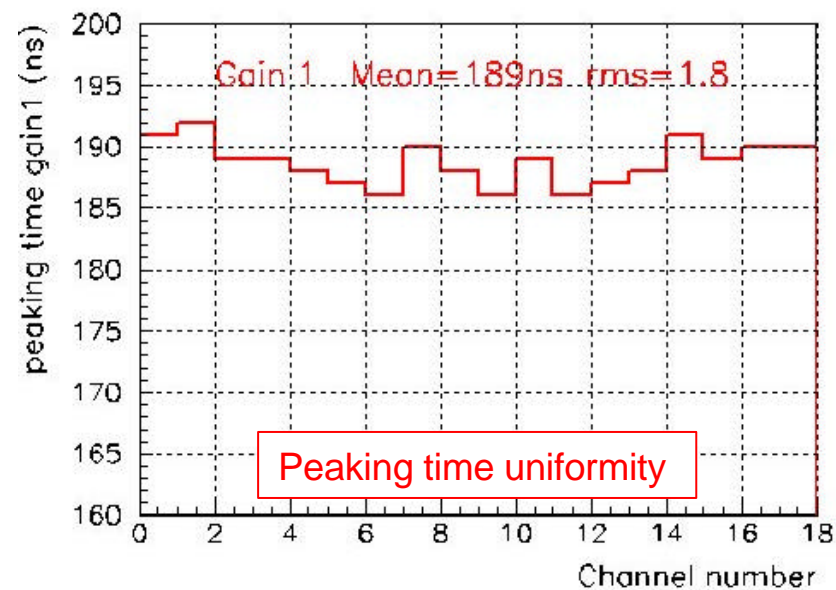
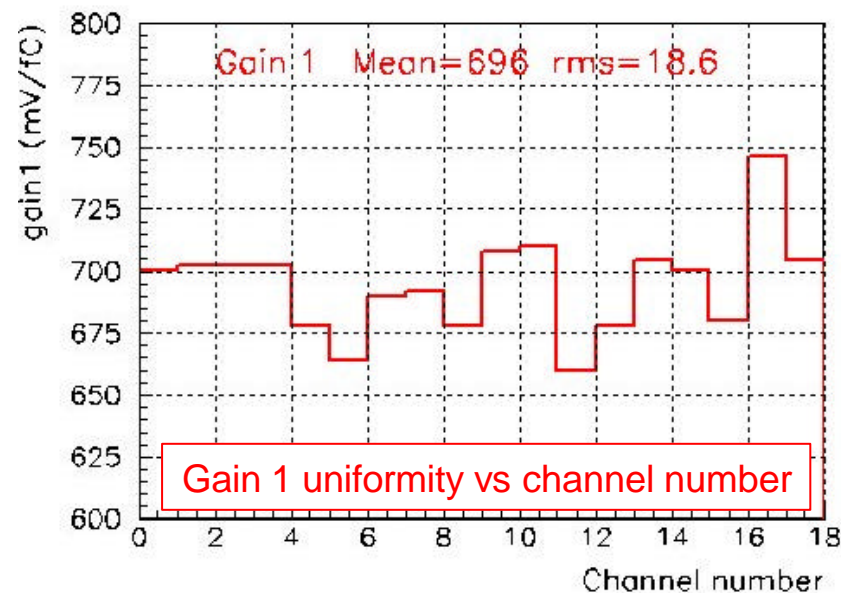
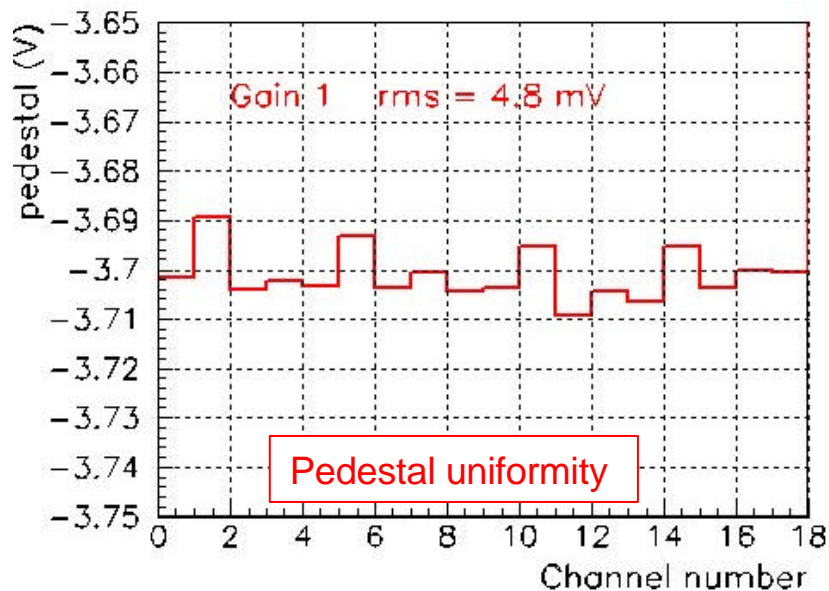
## ■ Signal (Gain 1, $C_f=1.6\text{pF}$ )

- Amplitude =  $696 \text{ mV/pC} \pm 18 \text{ mV}$   
=  $4.66 \text{ mV/ MIP} \pm 2.5\% \text{ rms}$
- Peaking time =  $189 \text{ ns} \pm 2 \text{ ns rms}$
- Pedestals =  $-3.7 \text{ V} \pm 4.8 \text{ mV rms}$

## ■ Noise

- $C_d = 0 \text{ pF}$  :  $V_n = 200 \text{ } \mu\text{V}$
- $C_d = 68 \text{ pF}$  :  $V_n = 410 \text{ } \mu\text{V}$

## ■ Crosstalk : < 0.1%



# Signal uniformity (G10)

## ■ Signal (Gain 10, Cf=1.6pF)

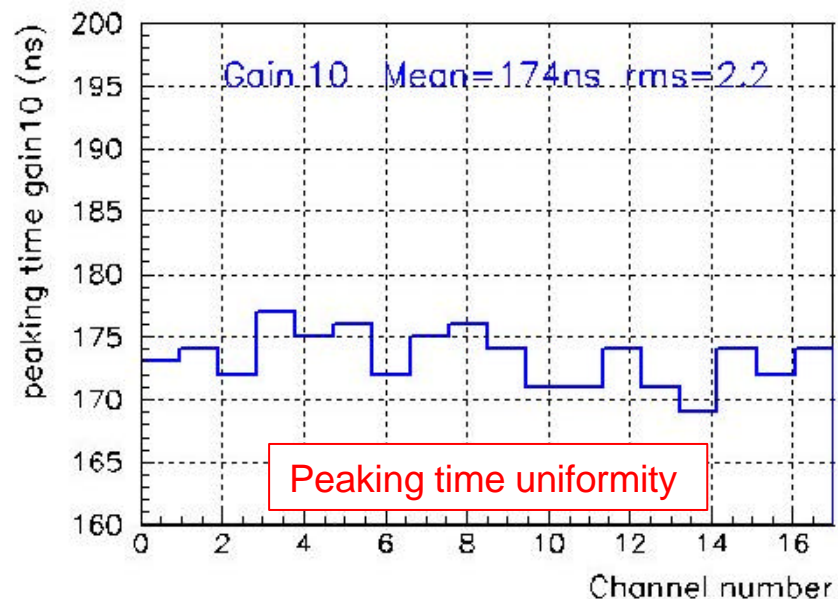
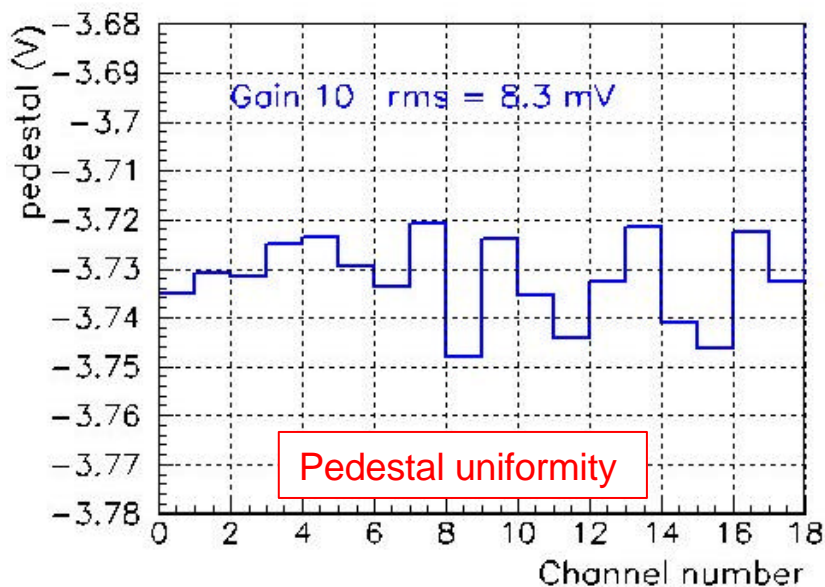
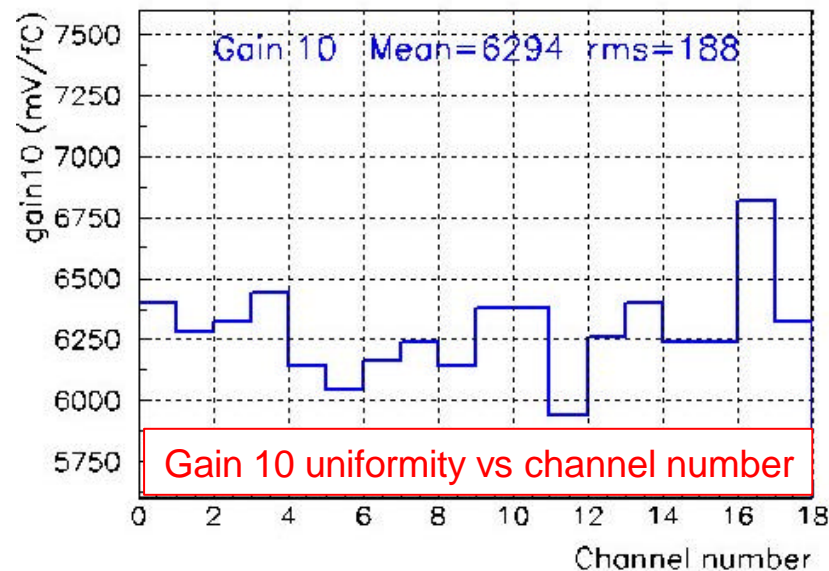
- Amplitude = 3147 mV/pC  $\pm$  94
- Peaking time = 174 ns  $\pm$  2 ns
- Pedestals = -3.74 V  $\pm$  8.3 mV rms

## ■ Noise

- Cd = 0 pF : Vn = 500  $\mu$ V
- Cd = 68pF : Vn = 1.6 mV

## ■ Crosstalk

- < 0.2%



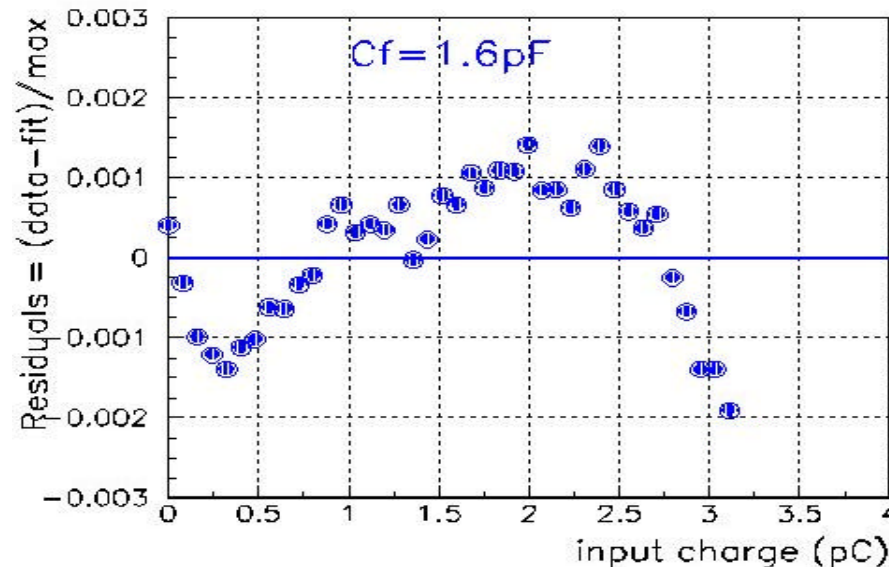
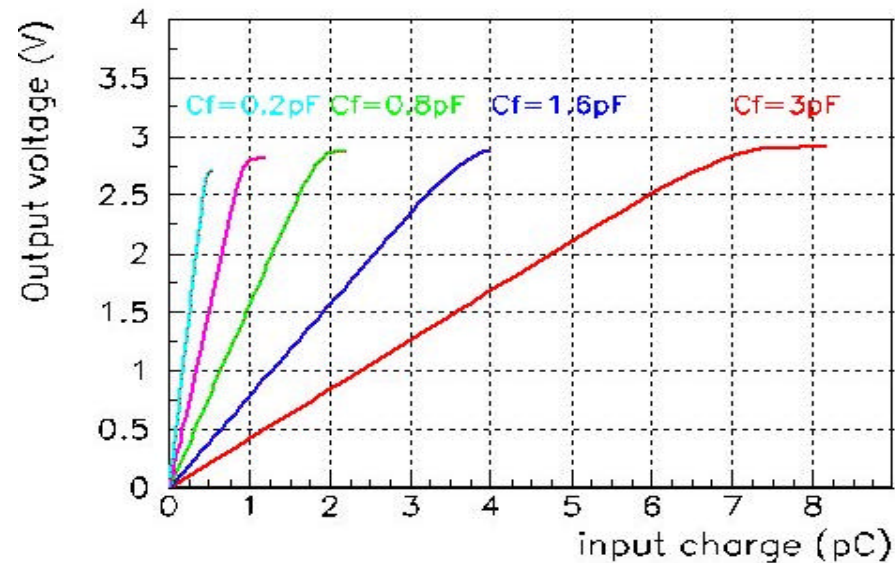
# Linearity

## ■ Measured on all preamp gains

- $C_f = 0.2, 0.4, 0.8, 1.6, 3 \text{ pF}$
- Well within  $\pm 0.2 \%$

## ■ Dynamic range ( $G1, C_f=1.6\text{pF}$ )

- Max output : 3 V
- linear (0.1%) range : 2.5V  
= **500 MIPS @  $C_f = 1.6 \text{ pF}$**
- Noise :
  - 200  $\mu\text{V}$  ( $C_d = 0$ )
  - 410  $\mu\text{V}$  ( $C_d = 68\text{pF}$ )
  - = **0.1 MIP @  $C_d = 68 \text{ pF}$**
- Dynamic range : **> 12 bits**
  - 13 000 (14 bits) @  $C_d = 0$
  - 6500 (12 bits) @  $C_d = 68 \text{ pF}$
- Can be easily extended by using the bi-gain outputs



# Results with detector

## ■ Cosmic test bench at LLR

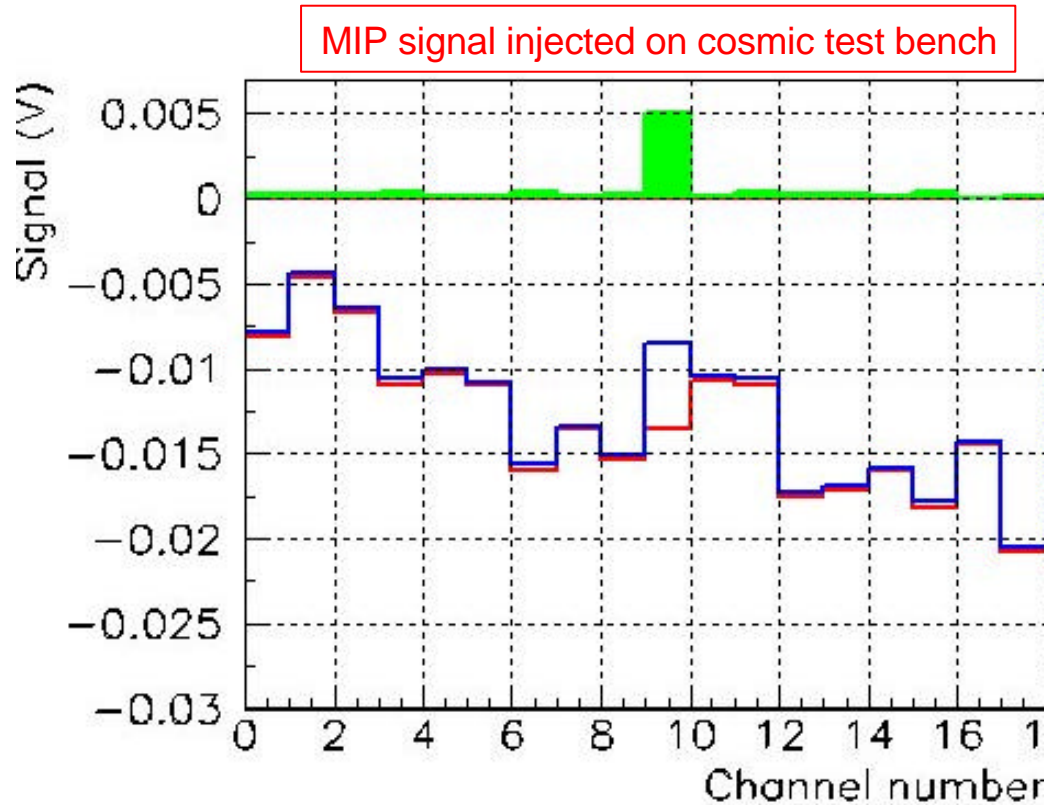
- 1 MIP injected in channel 9
- Calculation : 4.97 mV
- Measurement : 5.05 mV
- Well visible above the noise

## ■ MIP signal with $^{90}\text{Sr}$ source

- *See talk by J.C. Brient*

## ■ Readout boards

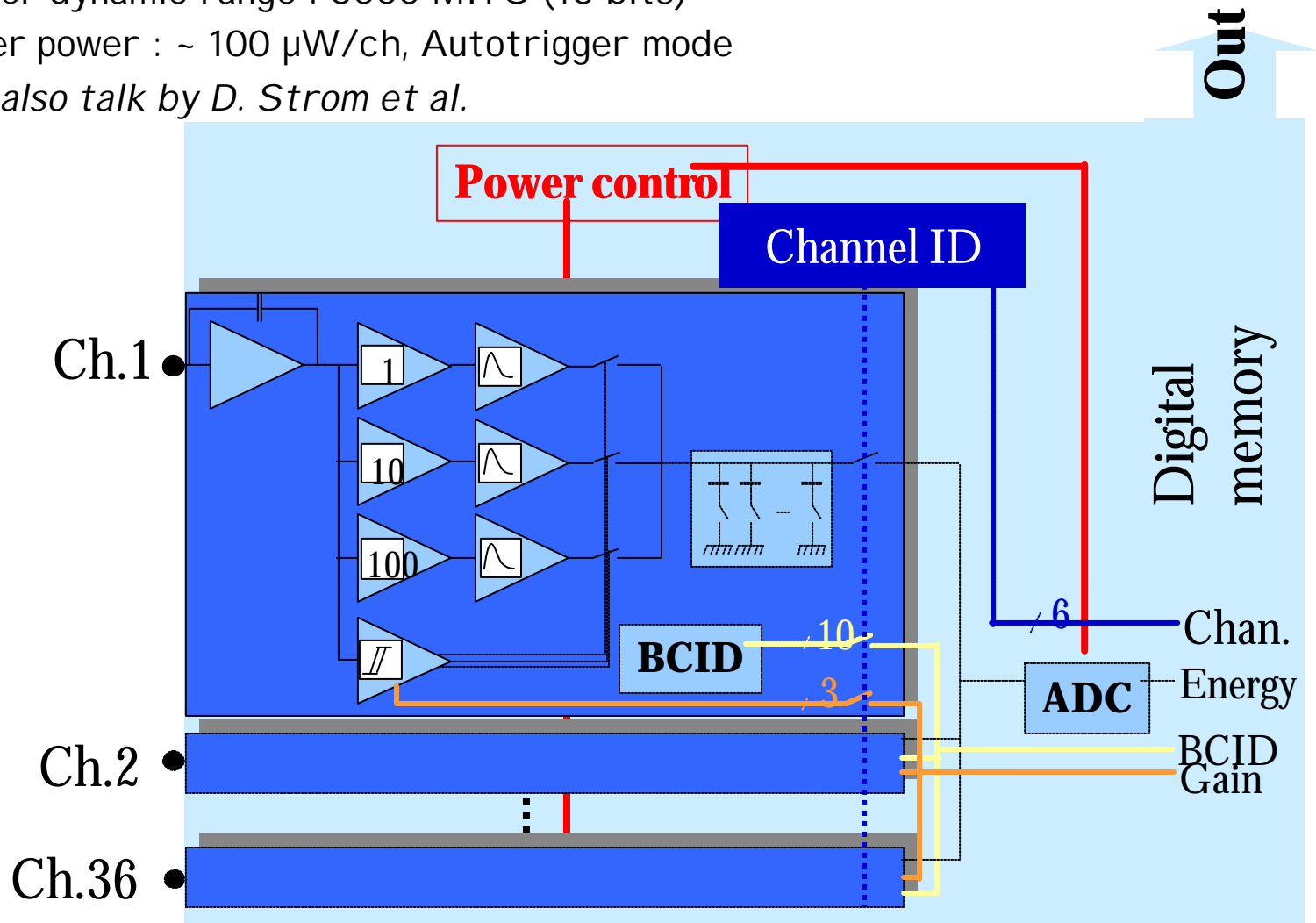
- Developed by UK group  
*[P. Dauncey Imperial college]*



# Next steps

## R&D on technological prototype

- Larger dynamic range : 3000 MIPS (16 bits)
- Lower power :  $\sim 100 \mu\text{W}/\text{ch}$ , Autotrigger mode
- See also talk by D. Strom et al.



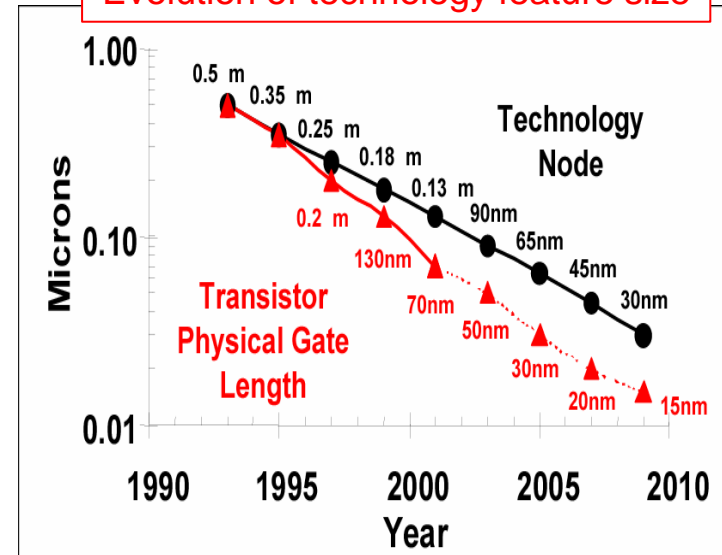


# Next steps : technological prototype

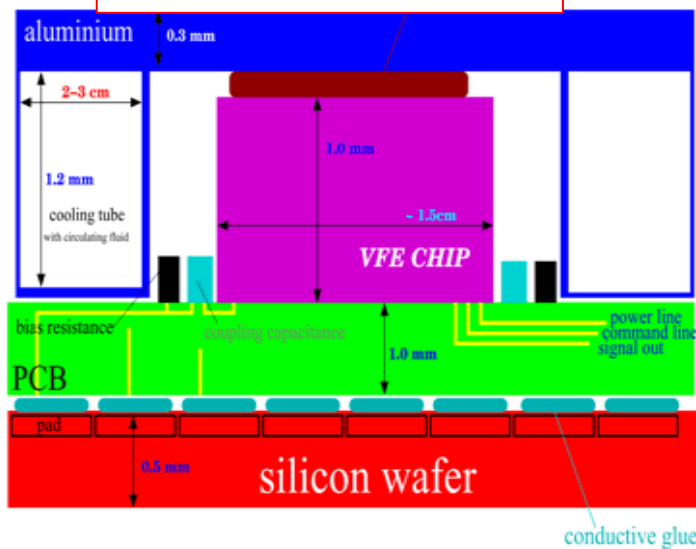
## Pending questions

- What **technology** to target for 2010-2020?
- What about **signal integrity** on a 16bit mixed-signal chip ?
- When to digitize ? Can we have **1 ADC /channel** ?
- What **(low) power** level can be reached ?

Evolution of technology feature size



Embedded readout ASIC



Signal integrity on mixed-signal ASICs



# Conclusion

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## ■ FLCPHY3 chip fulfills FLC Wsi testbeam prototype

- Low Noise :  $4000e^- = 0.1 \text{ MIP}$
- Maximum signal : 600 MIPs
- Linearity : 0.1%, crosstalk 0.1%
- Low pedestal dispersion : 4.8mV rms = 1 MIP
- Can fit other detectors (variable gain 0.2-3pF, bi-gain G1-G10 shaper)

## ■ 1000 chips have been produced for 2004-2005 testbeam

## ■ Next steps

- Low power developments for technological prototype
- New chip in SiGe  $0.35\mu\text{m}$  with Idle mode
- Trying to integrate the ADC...

